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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete if Known	
Application Number	10/721585
Filing Date	November 25, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	~~2825~~ 2891
Examiner Name	~~Unknown~~ C. Everhart
Attorney Docket No: 1303.017US2	

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Examiner Initials*	Cite No[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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EXAMINER C. Everhart DATE CONSIDERED 1-7-05

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	~~Unknown~~ 10/721,585
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First Named Inventor	Forbes, Leonard
Group Art Unit	~~Unknown~~ ~~2826~~ 2891
Examiner Name	~~Unknown~~ C. Everhart

Sheet 1 of 2

Attorney Docket No: 1303.017US2

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Substitute Disclosure Statement Form (PTO-1449)

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	Filing Date	~~Even Date Herewith~~ 11/25/03
	First Named Inventor	Forbes, Leonard
	Group Art Unit	~~Unknown~~ ~~2826~~ 2891
	Examiner Name	~~Unknown~~ C. Everhart
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